

AF/2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

ROBERT H. HAVEMANN ET AL.

Serial No. 09/216,214 (TI-21570)

Filed December 18, 1998

For: ENHANCEMENT TO POLYSILICON GATE

Art Unit 2811

Examiner T. Tran

Assistant Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.116

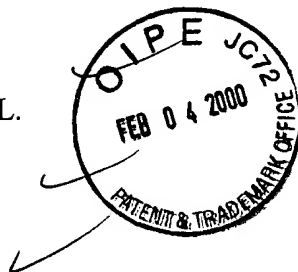
In response to the Office action dated January 7, 2000, please amend the above identified application as follows:

In the claims:

Amend claim 8 as follows:

8. (Twice Amended) A product by the method of forming a transistor structure, comprising the steps of:

- (a) forming a gate dielectric over a semiconductor region;
- (b) forming a patterned gate over said gate dielectric;



TC 1-1000-10011

#9/C
Amend. N.E.
Imma
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Do not enter. TT